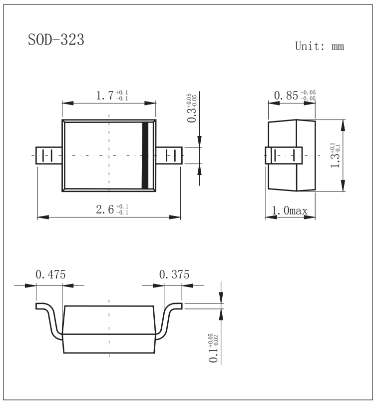
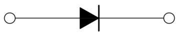
Schottky Diodes

BAT60B (KAT60B)





■ Features

- High Current Rectifier Schottky Diode with Low V_F Drop
- Low Voltage, Low Inductance
- For Power Supply
- For Detection and Step-up-Conversion

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
DC Blocking Voltage	V_R	10	V
Forward Current	I_F	3	A
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I_{FSM}	5	
Power Dissipation	P_D	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	286	℃/W
Junction Temperature	T_J	125	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	I_R= 1 mA	10			V
Forward voltage	V_{F1}	I_F= 100 mA			0.38	
	V_{F2}	I_F= 500mA			0.5	
	V_{F3}	I_F= 1000 mA			0.6	
Reverse voltage leakage current	I_{R1}	V_R=5 V			15	uA
	I_{R2}	V_R=8 V			25	
Capacitance between terminals	C_T	V_R= 5 V, f= 1MHz		30		pF

■ Marking

Marking	SL

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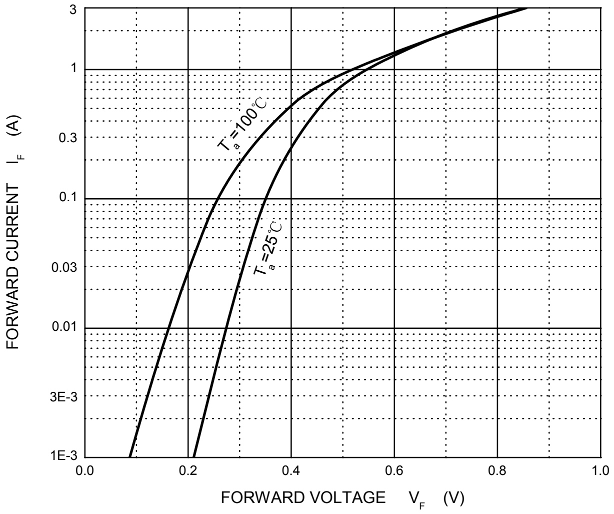
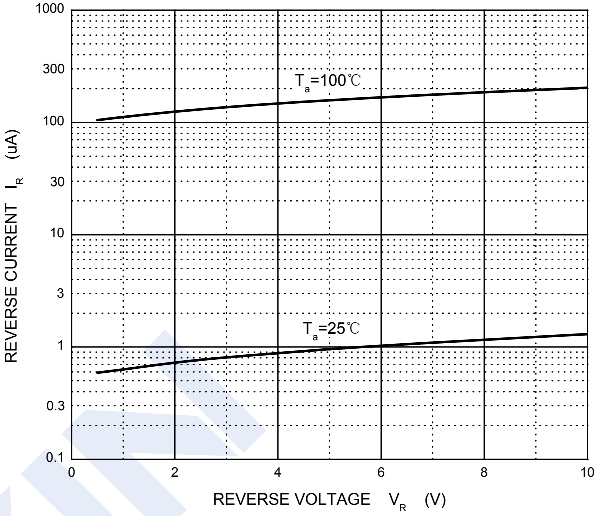
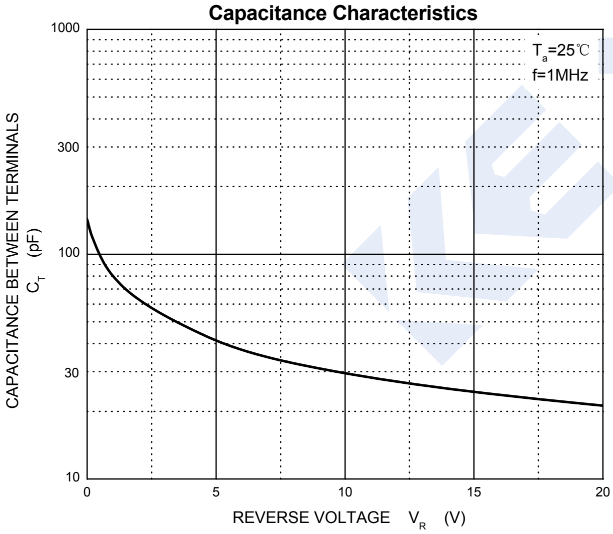
■ Typical Characterisitics



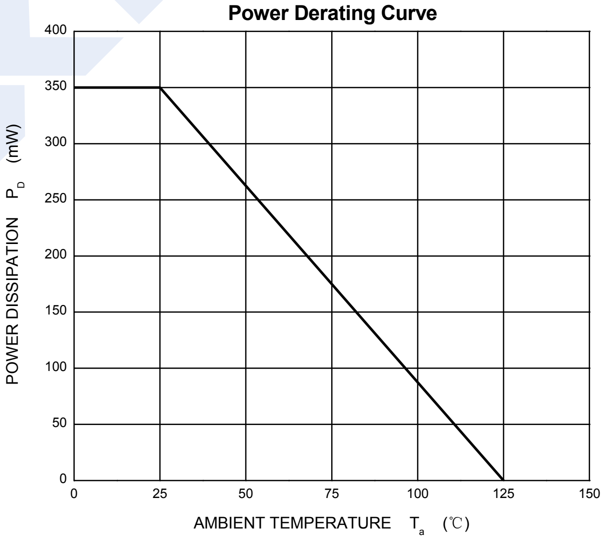
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve